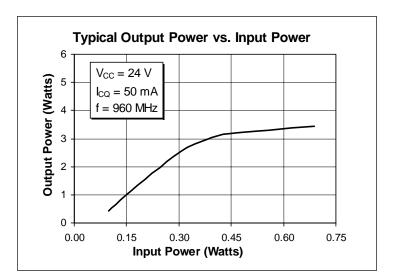


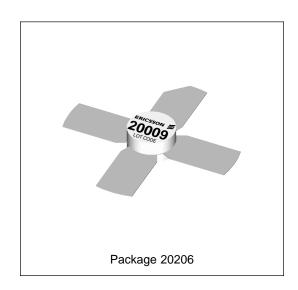
PTB 20009 2.5 Watts, 935–960 MHz Cellular Radio RF Power Transistor

Description

The 20009 is a class AB, NPN, common emitter RF power transistor intended for 24 Vdc operation across the 935 to 960 MHz frequency band. Rated at 2.5 Watts minimum output power, it may be used for both CW and PEP applications. Ion implantation, nitride surface passivation and gold metallization are used to ensure excellent device reliability. 100% lot traceability is standard.



- 2.5 Watts, 935–960 MHz
- Class AB Characteristics
- 50% Collector Efficiency at 2.5 Watts
- Gold Metallization
- Silicon Nitride Passivated



Maximum Ratings

Parameter	Sy	mbol	Value	Unit
Collector-Emitter Voltage	V	CER	40	Vdc
Collector-Base Voltage	V	′сво	50	Vdc
Emitter-Base Voltage (collector open)	V	'ЕВО	4.0	Vdc
Collector Current (continuous)		I _C	1.7	Adc
Total Device Dissipation at T _{flange} = 25°C Above 25°C derate by		P _D	13.5 0.077	Watts W/°C
Storage Temperature Range	Т	STG	-40 to +150	°C
Thermal Resistance (Tflange = 70°C)	F	R _{OJC}	13.0	°C/W

PTB 20009



Electrical Characteristics (100% Tested)

Characteristic	Conditions	Symbol	Min	Тур	Max	Units
Breakdown Voltage C to E	I _B = 0 A, I _C = 50 mA	V _{(BR)CEO}	25	30	_	Volts
Breakdown Voltage C to E	V _{BE} = 0 V, I _C = 50 mA	V _{(BR)CES}	55	70	_	Volts
Breakdown Voltage E to B	I _C = 0 A, I _E = 5 mA	V _{(BR)EBO}	3.5	5	_	Volts
DC Current Gain	V _{CE} = 5 V, I _C = 250 A	h _{FE}	20	50	120	_

RF Specifications (100% Tested)

Characteristic	Symbol	Min	Тур	Max	Units
Gain					
(V _{CC} = 24 Vdc, P _{out} = 2.5 W, I _{CQ} = 50 mA, f = 935–960 MHz)	G _{pe}	9	10	12	dB
Collector Efficiency					
(V _{CC} = 24 Vdc, P _{out} = 2.5 W, I _{CQ} = 50 mA, f = 935–960 MHz)	ηC	50	_	_	%
Load Mismatch Tolerance					
(V _{CC} = 24 Vdc, P _{Out} = 2.5 W, I _{CQ} = 50 mA, f = 935–960 MHz, —all phase angles at frequency of test)	Ψ	_	_	30:1	_

Typical Performance

